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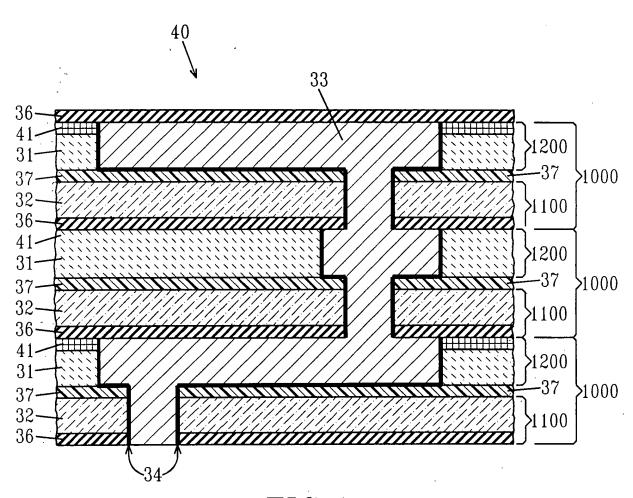


FIG.1

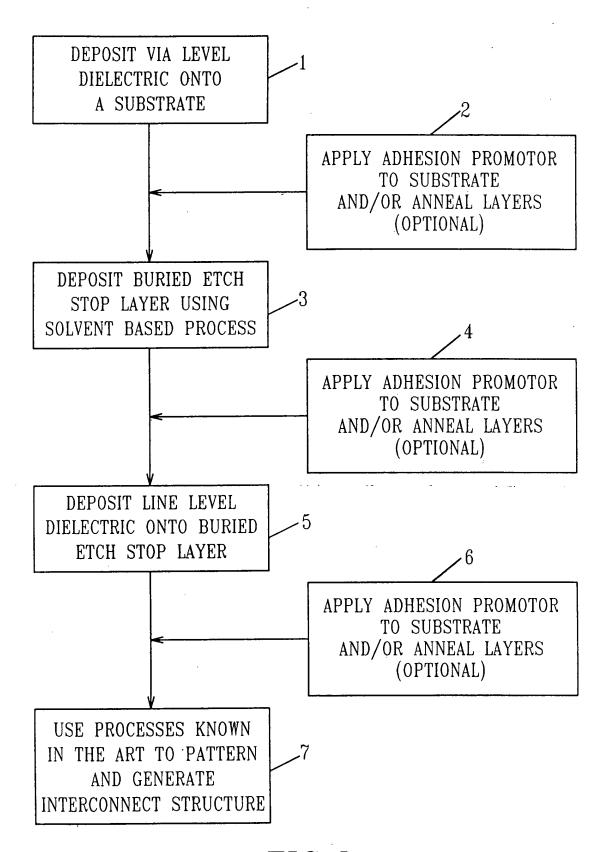


FIG.2

Figure 3: Scanning Electron Micrograph of Trilayer Film Having a Buried Etch Stop Layer Mag = 300.85 K X Polycarbosilane Buried (thickness=200nm) (thickness=215nm) Porous Line Level (thickness=26nm) Etch Stop Layer Porous Via Level Dielectric Dielectric